

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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# 2SB1079

Silicon PNP Triple Diffused

**RENESAS**

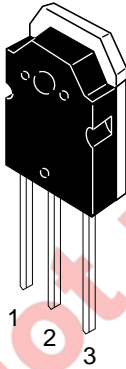
ADE-208-866 (Z)  
1st. Edition  
September 2000

## Application

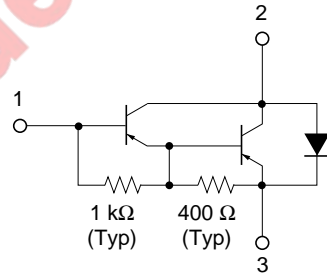
Low frequency power amplifier complementary pair with 2SD1559

## Outline

TO-3P



1. Base
2. Collector (Flange)
3. Emitter



## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-100	V
Collector to emitter voltage	$V_{CEO}$	-100	V
Emitter to base voltage	$V_{EBO}$	-7	V
Collector current	$I_C$	-20	A
Collector peak current	$I_{C(peak)}$	-30	A
Base current	$I_B$	-3	A
Collector power dissipation	$P_C^{*1}$	100	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

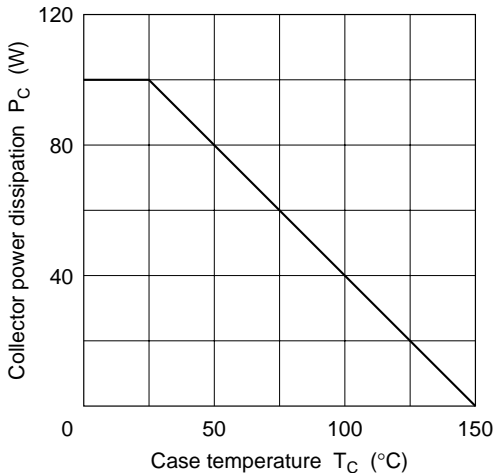
Note: 1. Value at  $T_C = 25^\circ\text{C}$ .

## Electrical Characteristics (Ta = 25°C)

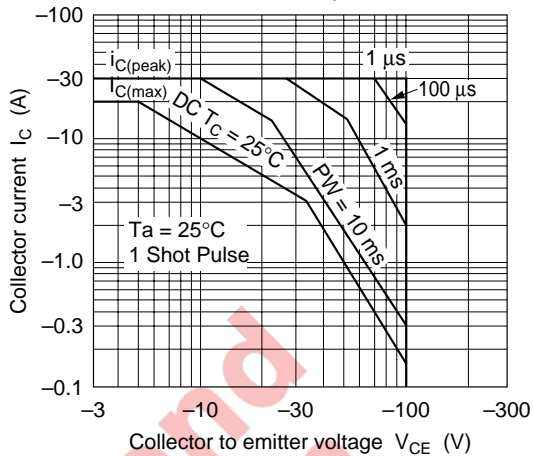
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-100	—	—	V	$I_C = -0.1\text{ mA}$ , $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-100	—	—	V	$I_C = -25\text{ mA}$ , $R_{BE} = \infty$
Collector to emitter sustain voltage	$V_{CEO(sus)}$	-100	—	—	V	$I_C = -200\text{ mA}$ , $R_{BE} = \infty^{*1}$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	—	—	V	$I_E = -50\text{ mA}$ , $I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	-100	$\mu\text{A}$	$V_{CB} = -100\text{ V}$ , $I_E = 0$
	$I_{CEO}$	—	—	-1.0	mA	$V_{CE} = -80\text{ V}$ , $R_{BE} = \infty$
DC current transfer ratio	$h_{FE}$	1000	—	20000		$V_{CE} = -3\text{ V}$ , $I_C = -10\text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	-2.0	V	$I_C = -10\text{ A}$ , $I_B = -20\text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	-2.5	V	
Collector to emitter saturation voltage	$V_{CE(sat)2}$	—	—	-3.0	V	$I_C = -20\text{ A}$ , $I_B = -200\text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)2}$	—	—	-3.5	V	
Turn on time	$t_{on}$	—	0.6	—	$\mu\text{s}$	$I_C = -10\text{ A}$ , $I_{B1} = -I_{B2} = -20\text{ mA}$
Storage time	$t_{stg}$	—	3.5	—	$\mu\text{s}$	

Note: 1. Pulse Test.

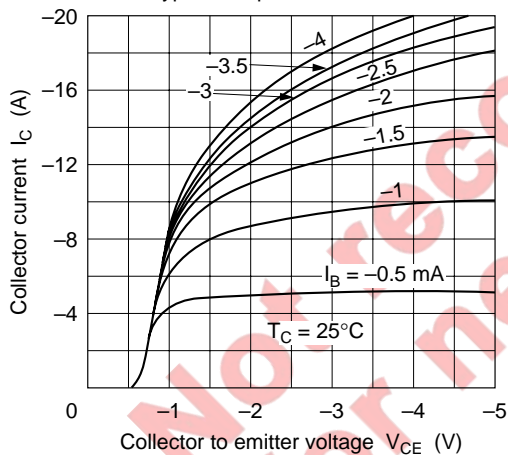
Maximum Collector Dissipation Curve



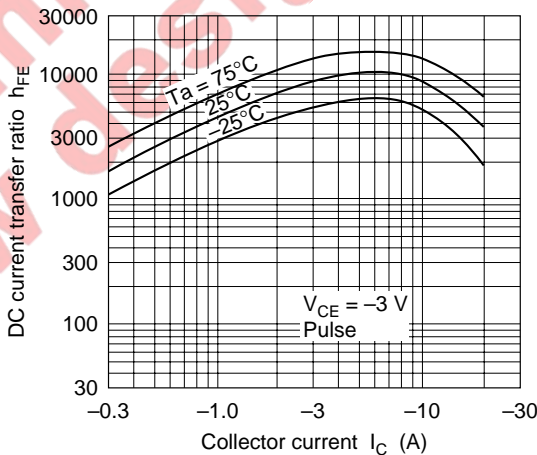
Area of Safe Operation



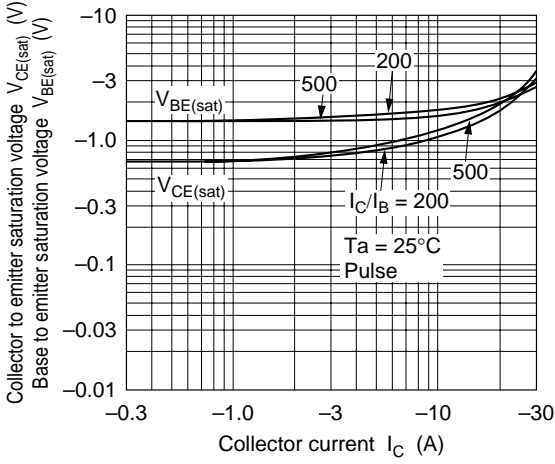
Typical Output Characteristics



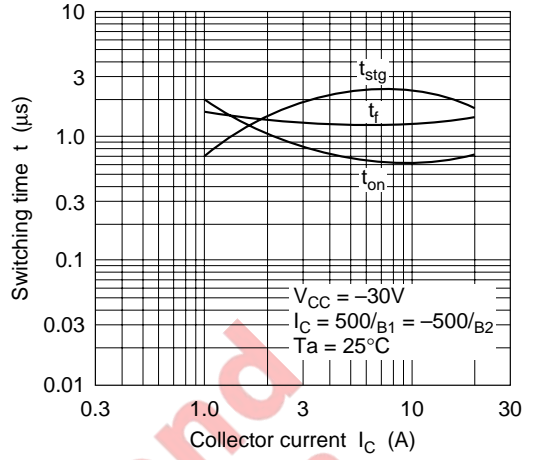
DC Current Transfer Ratio vs. Collector Current



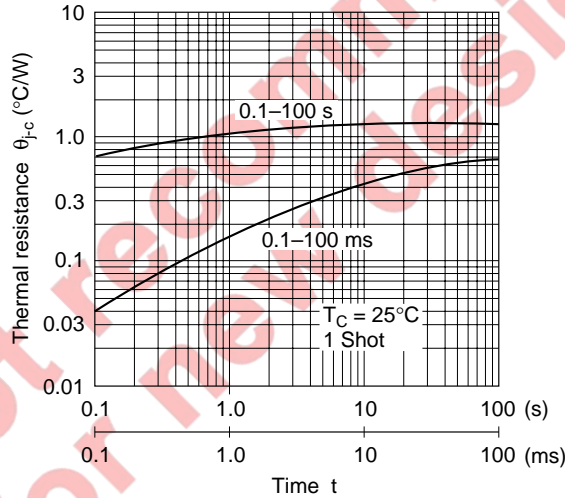
Saturation Voltage vs. Collector Current



Switching Time vs. Collector Current



Transient Thermal Resistance



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